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### BC307/308/309

### **Switching and Amplifier Applications**

• Low Noise: BC309



## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CES</sub>	Collector-Emitter Voltage			
	: BC307	-50	V	
	: BC308/309	-30	V	
$V_{CEO}$	Collector-Emitter Voltage			
	: BC307	-45	V	
	: BC308/309	-25	V	
$V_{EBO}$	Emitter-Base Voltage	-5	V	
I <sub>C</sub>	Collector Current (DC)	-100	mA	
P <sub>C</sub>	Collector Power Dissipation	500	mW	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristi	<b>CS</b> T <sub>a</sub> =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage : BC307 : BC308/309	I <sub>C</sub> = -2mA, I <sub>B</sub> =0	-45 -25			V
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage : BC307 : BC308/309	I <sub>C</sub> = -10μA, V <sub>BE</sub> =0	-50 -30			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -10μA, I <sub>C</sub> =0	-5			V
I <sub>CES</sub>	Collector Cut-off Current : BC307 : BC308/309	V <sub>CE</sub> = -45V, V <sub>BE</sub> =0 V <sub>CE</sub> = -25V, V <sub>BE</sub> =0		-2 -2	-15 -15	nA nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	120		800	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-0.5	-0.3	V V
V <sub>BE</sub> (sat)	Collector-Base Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-0.7 -0.85		V V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	-0.55	-0.62	-0.7	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f=50MHz		130		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz			6	pF
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> = -0.5V, I <sub>C</sub> =0, f=1MHz		12		pF
NF	Noise Figure	$V_{CE}$ = -5V, $I_{C}$ = -0.2mA, $R_{G}$ =2K $\Omega$ , f=1KHz $V_{CE}$ = -5V, $I_{C}$ = -0.2mA $R_{G}$ =2K $\Omega$ , f=30~15KHz		2	10 4 4	dB dB dB

# h<sub>FE</sub> Classification

Classification	А	В	С
h <sub>FE</sub>	120 ~ 220	180 ~ 460	380 ~ 800

## **Typical Characteristics**

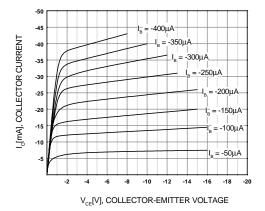


Figure 1. Static Characteristic

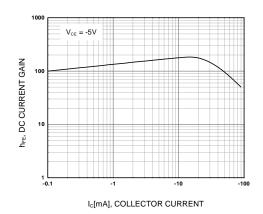


Figure 2. DC current Gain

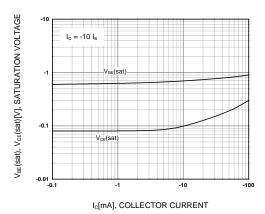


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

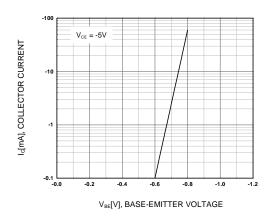


Figure 4. Base-Emitter Capacitance

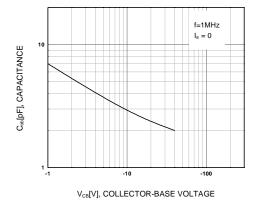


Figure 5. Collector Output Capacitance

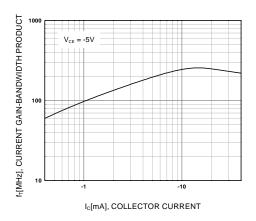
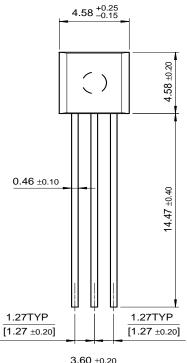
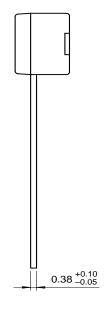


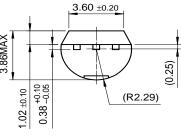
Figure 6. Current Gain Bandwidth Product

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franci	hise™	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX <sup>TM</sup>
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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